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AMENDMENT TO CLAIMS

In the Claims:

Please **AMEND** claims 3-6.

Please **ADD** new claims 9-15.

A copy of all pending claims and a status of each is provided below.

1. (Previously Presented) A thin film transistor array panel, comprising:

an insulating substrate;

a gate line formed on the substrate;

a plurality of storage electrodes formed on the substrate, each storage electrode including a plurality of branches;

a gate insulating layer formed on the gate line and the storage electrode;

a semiconductor layer formed on the gate insulating layer;

a data conductor formed on the data conductor layer; and

a pixel electrode layer formed on the passivation layer,

wherein at most one of the branches of each storage electrode has an isolated end.

2. (Previously Presented) The thin film transistor array panel of claim 1, wherein longitudinal portions of adjacent storage electrodes are connected by connecting portions.

3. (Currently Amended) The thin film transistor array panel of claim 1, further comprising a connection bridge having a portion thereof connected to each of the isolated

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ends of the plurality of storage ~~conductors~~ electrodes and a portion thereof connected to a storage electrode line formed on the substrate.

4. (Currently Amended) The thin film transistor array panel of claim 1, wherein each storage ~~conductor~~ electrode further comprises two longitudinal branches and two oblique branches, and the branches of each storage conductor form a closed loop.

5. (Currently Amended) The thin film transistor array panel of claim 1, wherein each storage ~~conductor~~ electrode comprises two longitudinal branches connected to three oblique branches, the connected branches forming two closed loops.

6. (Currently Amended) The thin film transistor array panel of claim 1, wherein each storage ~~conductor~~ electrode comprises two longitudinal branches connected to four oblique branches, the connected branches forming three closed loops.

7. (Previously Presented) The thin film transistor array panel of claim 1, wherein the pixel electrode has a plurality of cutouts, and at least one of the cutouts overlaps the storage electrode.

8. (Previously Presented) The thin film transistor panel of claim 1, wherein the data conductor has substantially the same planar shape as the semiconductor layer except for a channel portion of the semiconductor layer.

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9. (New) A thin film transistor array panel, comprising:

an insulating substrate;

a gate line formed on the substrate;

a plurality of storage electrodes formed on the substrate, each storage electrode including a plurality of branches;

a gate insulating layer formed on the gate line and the storage electrode;

a semiconductor layer formed on the gate insulating layer;

a data conductor formed on the data conductor layer; and

a pixel electrode layer formed on the passivation layer,

wherein at most one of the branches of each storage electrode has an isolated end, and

wherein longitudinal portions of adjacent storage electrodes are connected by connecting portions.

10. (New) The thin film transistor array panel of claim 9, further comprising a connection bridge having a portion thereof connected to each of the isolated ends of the plurality of storage electrodes and a portion thereof connected to a storage electrode line formed on the substrate.

11. (New) The thin film transistor array panel of claim 9, wherein each storage electrode further comprises two longitudinal branches and two oblique branches, and the branches of each storage conductor form a closed loop.

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12. (New) The thin film transistor array panel of claim 9, wherein each storage electrode comprises two longitudinal branches connected to three oblique branches, the connected branches forming two closed loops.

13. (New) The thin film transistor array panel of claim 9, wherein each storage electrode comprises two longitudinal branches connected to four oblique branches, the connected branches forming three closed loops.

14. (New) The thin film transistor array panel of claim 9, wherein the pixel electrode has a plurality of cutouts, and at least one of the cutouts overlaps the storage electrode.

15. (New) The thin film transistor panel of claim 9, wherein the data conductor has substantially the same planar shape as the semiconductor layer except for a channel portion of the semiconductor layer.